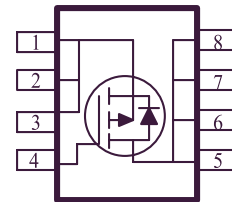


P-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize High Cell Density process. Low $r_{DS(on)}$ assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

- Low $r_{DS(on)}$ Provides Higher Efficiency and Extends Battery Life
- Miniature SO-8 Surface Mount Package Saves Board Space
- High power and current handling capability
- Extended VGS range (± 25) for battery pack applications

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ m(Ω)	I_D (A)
-30	30 @ $V_{GS} = -10V$	9.5
	52 @ $V_{GS} = -4.5V$	7.5



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 25	
Continuous Drain Current ^a	$T_A = 25^\circ\text{C}$	I_D	9.5	A
	$T_A = 70^\circ\text{C}$		8.3	
Pulsed Drain Current ^b		I_{DM}	± 50	
Continuous Source Current (Diode Conduction) ^a		I_S	-2.1	A
Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	3.1	W
	$T_A = 70^\circ\text{C}$		2.6	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Maximum	Units
Maximum Junction-to-Case ^a	$t \leq 5 \text{ sec}$	$R_{\theta JC}$	25	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^a	$t \leq 10 \text{ sec}$	$R_{\theta JA}$	50	$^\circ\text{C/W}$

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

SPECIFICATIONS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-30			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1	-1.6	-3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 25\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^\circ\text{C}$			-5	
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	-50			A
Drain-Source On-Resistance ^A	$r_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -9.5\text{ A}$		24	30	m Ω
		$V_{GS} = -4.5\text{ V}, I_D = -7.5\text{ A}$		44	52	
		$V_{GS} = -10\text{ V}, I_D = -9.5\text{ A}, T_J = 55^\circ\text{C}$		29	36	
Forward Tranconductance ^A	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -9.5\text{ A}$		31		S
Diode Forward Voltage	V_{SD}	$I_S = -2.1\text{ A}, V_{GS} = 0\text{ V}$		-0.7	-1.2	V
Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V},$ $I_D = -9.5\text{ A}$		15	26	nC
Gate-Source Charge	Q_{gs}			5.8		
Gate-Drain Charge	Q_{gd}			12		
Switching						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega, I_D = -1\text{ A},$ $V_{GEN} = -10\text{ V}, R_G = 6\Omega$		15	26	nS
Rise Time	t_r			12	21	
Turn-Off Delay Time	$t_{d(off)}$			62	108	
Fall-Time	t_f			46	71	

Notes

- Pulse test: $PW \leq 300\mu\text{s}$ duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

Typical Electrical Characteristics (P-Channel)

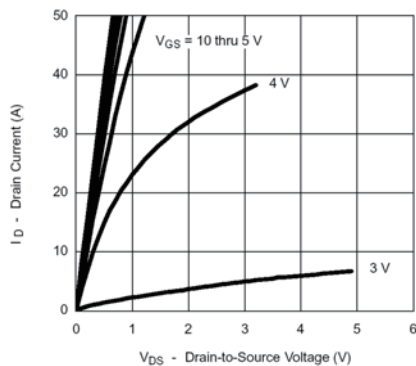


Figure 1. On-Region Characteristics

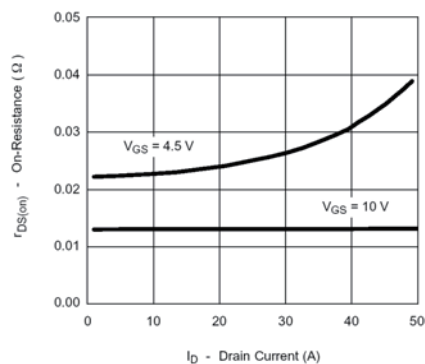


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

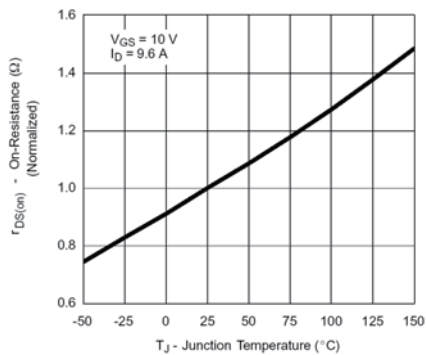


Figure 3. On-Resistance Variation with Temperature

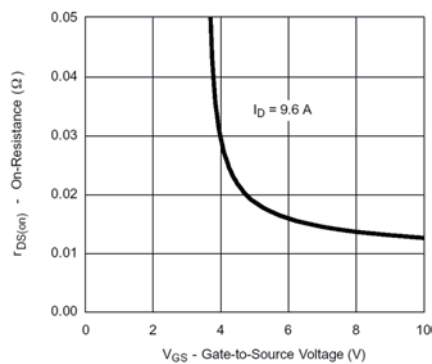


Figure 4. On-Resistance Variation with Gate to Source Voltage

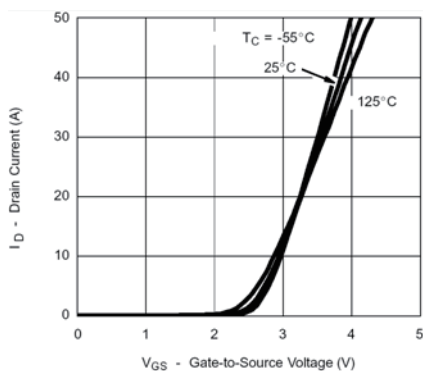


Figure 5. Transfer Characteristics

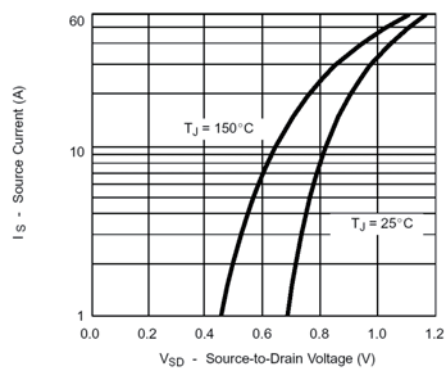


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Electrical Characteristics (P-Channel)

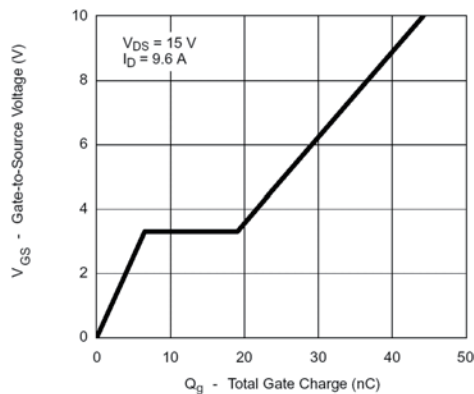


Figure 7. Gate Charge Characteristics

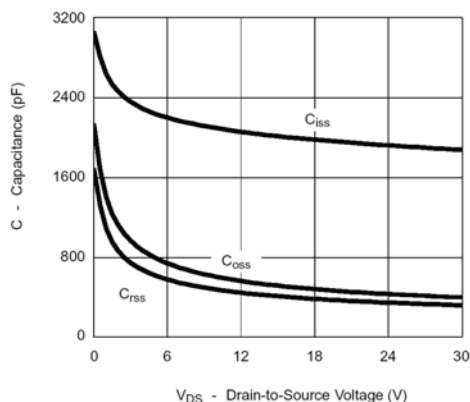


Figure 8. Capacitance Characteristics

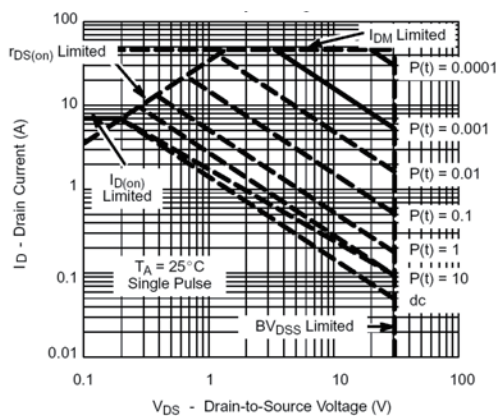


Figure 9. Maximum Safe Operating Area

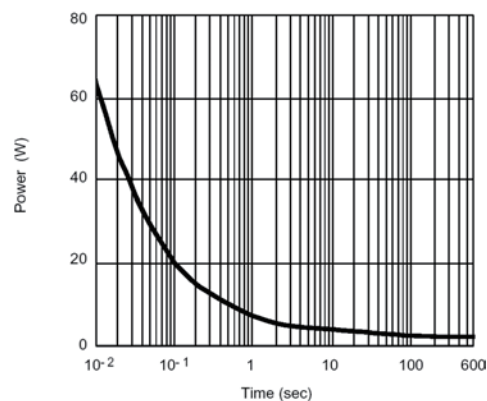


Figure 10. Single Pulse Maximum Power Dissipation

Normalized Thermal Transient Junction to Ambient

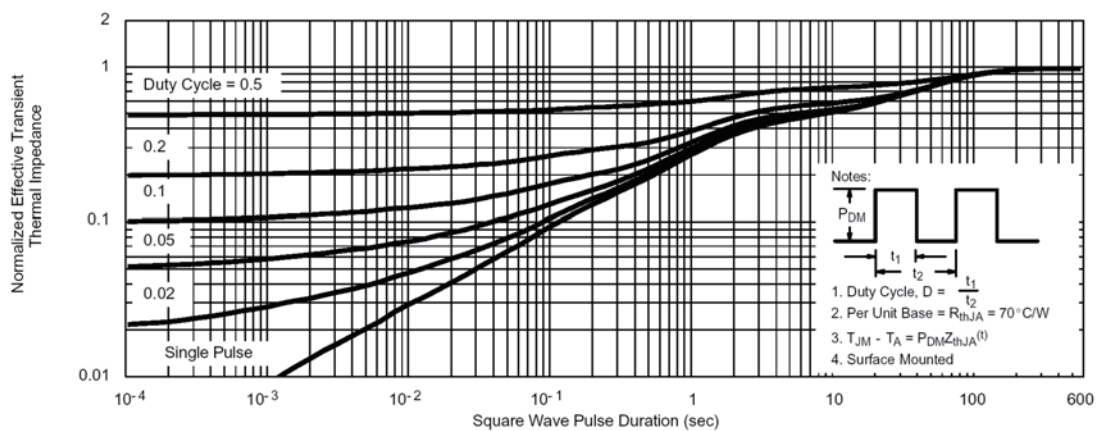
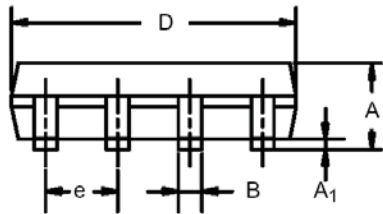
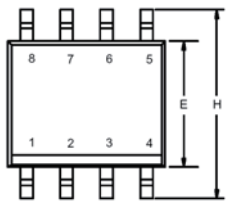


Figure 11. Transient Thermal Response Curve

Package Information

SO-8: 8LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°

